

II. Amendments to the Specification

1. Field of the Invention

Please replace the paragraph that begins at page 1 line 11 with the following amended paragraph:

This invention relates to a process for depositing gallium oxide coatings on a flat glass substrate[.]. More particularly, this invention relates to an atmospheric chemical vapor deposition process for producing gallium oxide coatings at high growth rates on flat glass using a coating precursor gas mixture comprising a gallium halide and an organicester.

Please replace the paragraph that begins at page 4 line 8 with the following amended paragraph:

While it is contemplated that the precursors could be combined at, or very near, the surface of the glass, the present invention involves the preparation of a precursor gas mixture which includes gallium chloride, particularly gallium trichloride $[(GaCl_3)]$ ($GaCl_3$) and an organic ester; a carrier gas or diluent, for example, nitrogen, air or helium, will normally also be included in the gas mixture. Since thermal decomposition of the organic ester may initiate the gallium oxide deposition reaction at a high rate, it is desirable that the precursor mixture be kept at a temperature below the thermal decomposition temperature of the organic ester to prevent prereaction of the gaseous mixture resulting in formation of the gallium oxide.

Please replace the paragraph that begins at page 8 line 20 with the following amended paragraph:

One such alternative distributor beam configuration generally introduces the precursor gas mixture through a gas supply duct where it is cooled by cooling fluid circulated through cooling ducts. ~~[[Gas]]~~ The gas supply duct opens through an elongated aperture into a gas flow restrictor.